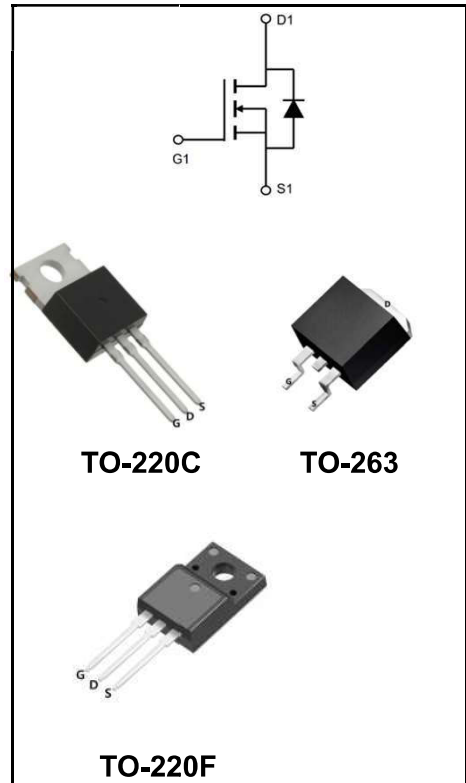


**600V N-CHANNEL ENHANCEMENT MODE MOSFET**

**MAIN CHARACTERISTICS**

<b>I<sub>D</sub></b>	10A
<b>V<sub>DSS</sub></b>	600V
<b>R<sub>DS(on)-typ(@V<sub>GS</sub>=10V)</sub></b>	<0.9Ω ( <b>Type:0.75Ω</b> )



**Features**

- ◆Fast Switching
- ◆Low ON Resistance
- ◆Low Gate Charge
- ◆100% Single Pulse avalanche energy Test
- ◆LeadfreeincomplywithEURoHS2011/65/EUdirectives

**Mechanical Data**

- ◆Case: Molded plastic
- ◆Mounting Position: Any
- ◆Molded Plastic: UL Flammability Classification Rating 94V-0
- ◆Solder bath temperature275℃maximum,10s per JESD22-106

**Product Specification Classification**

Part Number	Package	Marking	Pack
YFW10N60AC	TO-220C	YFW 10N60AC XXXXX	1000PCS/box
YFW10N60AF	TO-220F(0.5mm)	YFW 10N60AF XXXXX	1000PCS/box
YFW10N60AF	TO-220F(1.3mm)	YFW 10N60AF XXXXX	1000PCS/box
YFW10N60AS-G	TO-263	YFW 10N60AS XXXXX	1000PCS/box
YFW10N60AS	TO-263	YFW 10N60AS XXXXX	800PCS/Reel

**Maximum Ratings at Tc=25°C unless otherwise specified**

Characteristics	Symbols	Value			Units
		220C	220F	263	
Drain-Source Voltage	<b>V<sub>DS</sub></b>	600			<b>V</b>
Gate-Source Voltage	<b>V<sub>GS</sub></b>	±30			<b>V</b>
Continue Drain Current-Continuous (TC = 25°C)	<b>I<sub>D</sub></b>	10			<b>A</b>
-Continuous (TC = 100°C)		6			
Pulsed Drain Current (Note1)	<b>I<sub>DM</sub></b>	40			<b>A</b>
Power Dissipation	<b>P<sub>D</sub></b>	143	50	143	<b>W</b>
-Derate above 25°C		1.14	0.38	1.14	<b>W/°C</b>
Single Pulse Avalanche Energy (Note2)	<b>E<sub>AS</sub></b>	700			<b>mJ</b>
Avalanche Current (Note 1)	<b>I<sub>AR</sub></b>	10			<b>A</b>
Repetitive Avalanche Energy (Note 1)	<b>E<sub>AS</sub></b>	17			<b>mJ</b>
Operating Temperature Range	<b>T<sub>J</sub></b>	150			<b>°C</b>
Storage Temperature Range	<b>T<sub>STG</sub></b>	-55 to +150			<b>°C</b>
Thermal Resistance, Junction to Case	<b>R<sub>θJC</sub></b>	0.85	2.6	0.85	<b>°C/W</b>
Thermal Resistance, Junction to Ambient	<b>R<sub>θJA</sub></b>	62.5	62.5	62.5	<b>°C/W</b>

**Maximum Ratings at Tc=25°C unless otherwise specified**

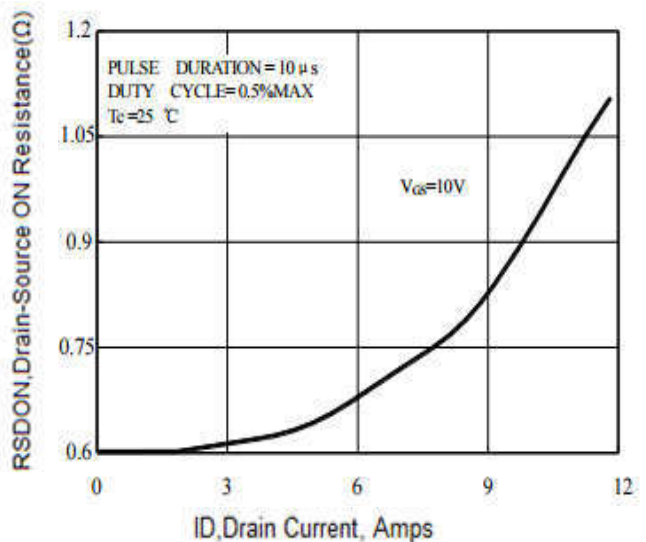
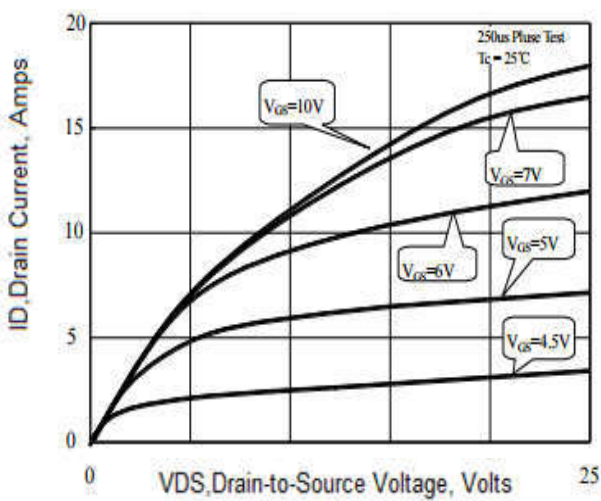
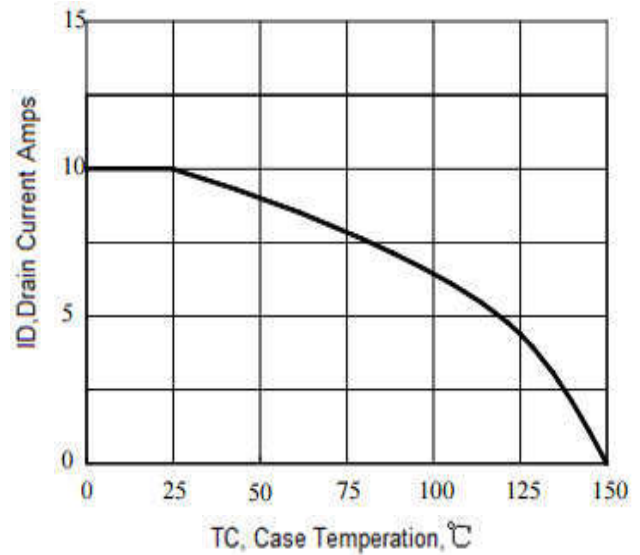
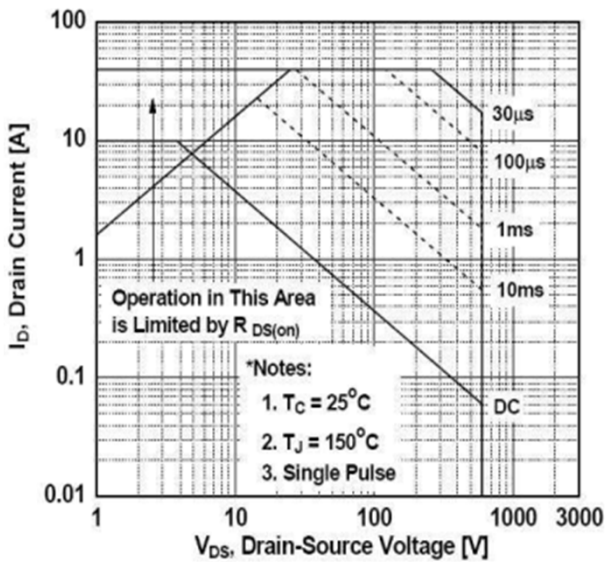
Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	<b>BV<sub>DSS</sub></b>	600	-	-	<b>V</b>
Drain-Source Leakage Current	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	<b>I<sub>DSS</sub></b>	-	-	1	<b>uA</b>
	V <sub>DS</sub> = 480 V, T <sub>c</sub> = 125°C		-	-	10	
Gate Leakage Current	V <sub>GS</sub> = ± 30 V, V <sub>DS</sub> = 0 V	<b>I<sub>GSS</sub></b>	-	-	±100	<b>nA</b>
Gate-Source Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	<b>V<sub>GS(th)</sub></b>	2	-	4	<b>V</b>
Drain-Source On-State Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A	<b>R<sub>DS(on)</sub></b>	-	0.75	0.9	<b>Ω</b>
Forward Transconductance(Note3)	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 5 A	<b>g<sub>fs</sub></b>	-	9.5	-	<b>S</b>
Input Capacitance	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1MHz	<b>C<sub>iss</sub></b>	-	1609	-	<b>pF</b>
Output Capacitance		<b>C<sub>oss</sub></b>	-	136	-	
Reverse Transfer Capacitance		<b>C<sub>rss</sub></b>	-	8	-	
Turn-on Delay Time	I <sub>D</sub> = 10 A, V <sub>DD</sub> = 300 V, R <sub>G</sub> = 25Ω(Note3,4)	<b>td(ON)</b>	-	26	-	<b>nS</b>
Rise Time		<b>tr</b>	-	23	-	
Turn-Off Delay Time		<b>td(OFF)</b>	-	49	-	
Fall Time		<b>tf</b>	-	27	-	
Total Gate Charge	I <sub>D</sub> = 10 A, V <sub>DD</sub> = 480V, V <sub>GS</sub> = 10 V(Note3,4)	<b>Q<sub>G</sub></b>	-	32	-	<b>nC</b>
Gate to Source Charge		<b>Q<sub>GS</sub></b>	-	8	-	
Gate to Drain Charge		<b>Q<sub>GD</sub></b>	-	12	-	

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

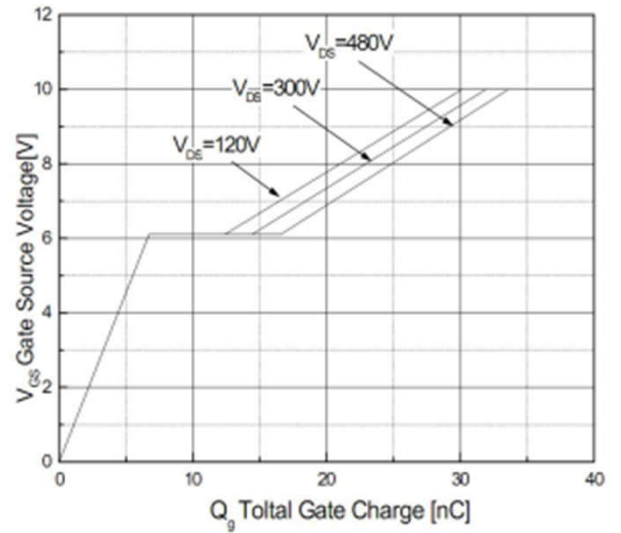
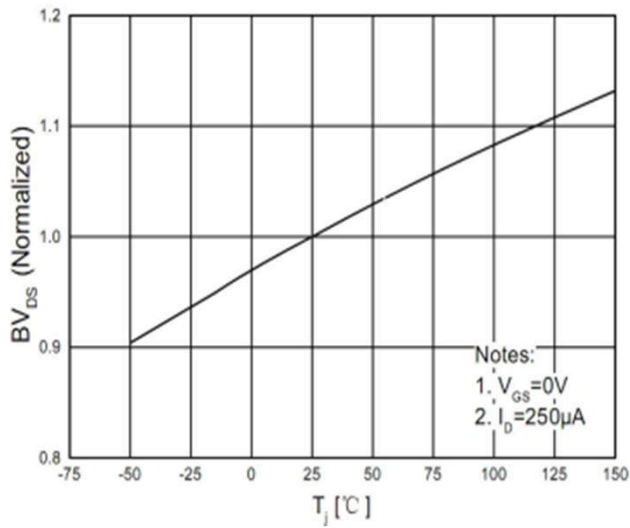
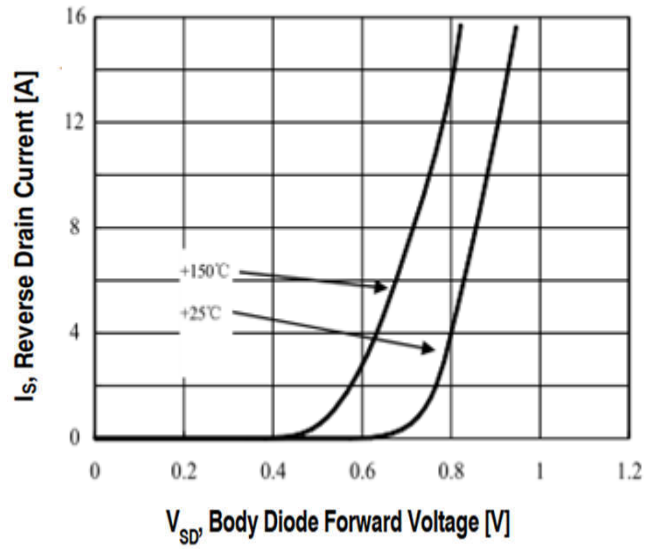
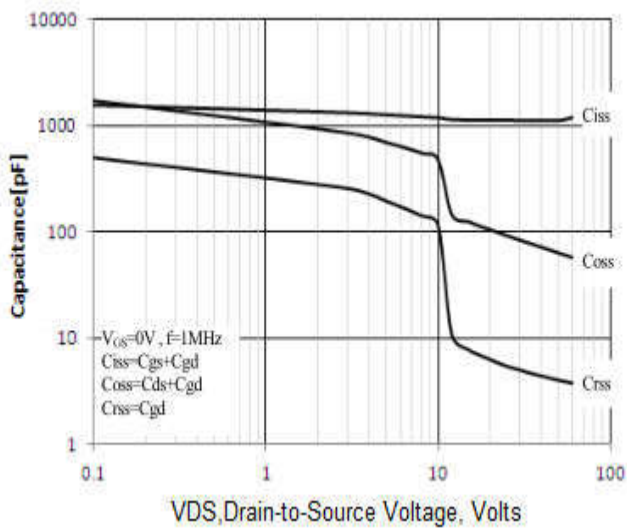
Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Maximum Continuous Drain-Source Diode Forward Current		<b>I<sub>S</sub></b>	-	-	10	<b>A</b>
Maximum Pulsed Drain-Source Diode Forward Current		<b>I<sub>SM</sub></b>	-	-	40	<b>A</b>
Drain-Source Diode Forward Voltage	I <sub>SD</sub> = 10 A	<b>V<sub>SD</sub></b>	-	-	1.4	<b>V</b>
Reverse Recovery Time	I <sub>SD</sub> = 10 A, V <sub>GS</sub> = 0 V, dI <sub>F</sub> / dt = 100 A/μs (Note3)	<b>trr</b>	-	500	-	<b>nS</b>
Reverse Recovery Charge		<b>Qrr</b>	-	3	-	<b>uC</b>

- Note:
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
  2. IAS = 10 A, VDD = 50 V, L = 14mH, RG = 25Ω, starting TJ = 25°C.
  3. ulse test: Pulse Width ≤300 μ s, Duty Cycle≤2%.
  4. Essentially Independent of Operating Temperature.

Ratings and Characteristic Curves



Ratings and Characteristic Curves



Package Outline Dimensions Millimeters

TO-220C

Dim.	Min.	Max.
A	9.8	10.2
A2	4.8	5.2
C	4.35	4.65
C1	1.45	1.05
D	0.65	0.95
E	3.45	3.75
F	2.85	3.15
G	6.4	6.8
H	0.35	0.65
J	28.68	28.98
K	2.8	3.2
M	1.15	1.45
N	Typical 2.54	
P	2.2	2.6
Q	9	9.4
S	0.15	0.35
U	2.65	2.95
DIA	宽1.50±0.10	
	深0.50 MAX	
All Dimensions in millimeter		

TO-220F

Dim.	Min.	Max.
A	9.95	10.25
B	2.95	3.25
C	1.25	1.45
D	12.95	13.25
E	0.50	0.65
F	3.1	3.3
G	1.30	1.45
H	Typ 2.54	
I	Typ 5.08	
J	4.60	4.75
K	2.50	2.65
L	6.35	6.55
M	15.4	16.0
N	2.75	3.05
O	0.48	0.52
P	0.76	0.84
All Dimensions in millimeter		

Package Outline Dimensions Millimeters

TO-263

	Dim.	Min.	Max.
	A	10.1	10.2
	B	7.4	7.6
	C	1.3	1.5
	D	0.55	0.75
	E	5.0	6.0
	F	1.4	1.6
	G	0.78	0.86
	H	1.2	1.3
	I	Typ2.54	
	J	8.4	8.6
	K	4.45	4.55
	L	1.25	1.35
	M	0.02	0.1
	N	2.4	2.8
O	0.36	0.40	
All Dimensions in millimeter			